查询IR207DM..CCB SERIES供应商

Bulletin I0139J 01/00

International
IOR Rectifier

IR207DM..CCB Series

STANDARD RECOVERY DIODES

- **Junction Size:** **Rectangular 207 x 157 mils**
- **Wafer Size:** **4"**
- **V_{RRM} Class:** **800 and 1200 V**
- **Passivation Process:** **Glassivated MOAT**
- **Reference IR Packaged Part:** **20ETS Series**

Major Ratings and Characteristics

Parameters		Units	Test Conditions	
V_{FM}	Maximum Forward Voltage	1100 mV	T_J = Amb., I_F = 20 A	
V_{RRM}	Reverse Breakdown Voltage Range	800 and 1200 V	T_J = Amb., I_{RRM} = 100 μA	**(1)**

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
Nominal Front Metal Composition, Thickness	100% Al, (20 μm)
Chip Dimensions	207 x 157 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	300 μm
Maximum Width of Sawing Line	45 μm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code

IR	207	D	M	12	C	CB
1	2	3	4	5	6	7

1 - International Rectifier Device

2 - Chip Dimension in Mils

3 - Type of Device: D = Wire Bondable Standard Recovery Diode

4 - Passivation Process: M = Glassivated MOAT

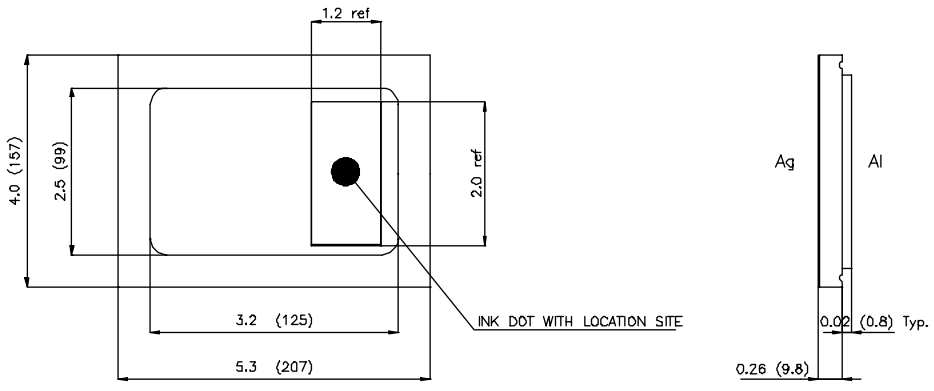
5 - Voltage code: Code x 100 = V_{RRM}

Available Class
08 = 800 V
12 = 1200 V

6 - Metallization: C = Aluminium (Anode) - Silver (Cathode)

7 - CB = Probed Uncut Die (wafer in box)
None = Probed Die in chip carrier

Outline Table

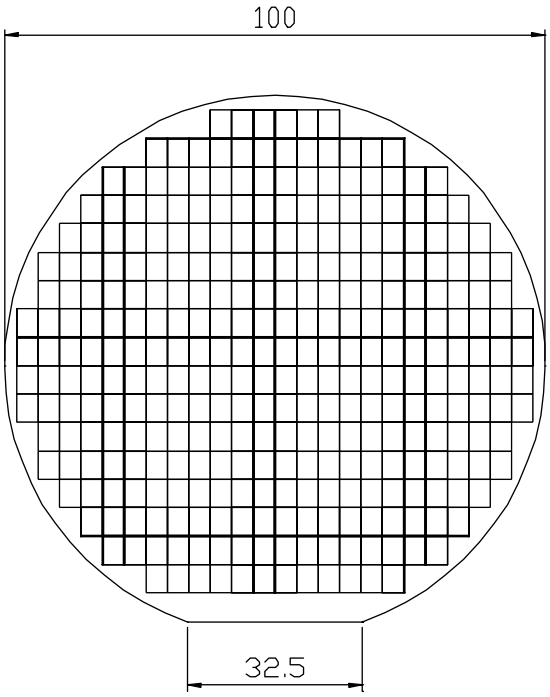


All dimensions are in millimeters

Wafer Layout

TOP VIEW

N° 304 Basic Cells



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